

Amendments to the Specification:

Please replace the abstract at page 11 with the following amended abstract:

~~--Radiation emitting semiconductor component~~

In a radiation-emitting semiconductor component with a layer structure comprising an n-doped confinement layer  $[(14)]$ , a p-doped confinement layer  $[(22)]$ , and an active, photon-emitting layer  $[(18)]$  disposed between the n-doped confinement layer  $[(14)]$  and the p-doped confinement layer  $[(22)]$ , it is provided according to the invention that the n-doped confinement layer  $[(14)]$  is doped with a first n-dopant (or two mutually different n-dopants) for producing high active doping and a sharp doping profile, and the active layer  $[(18)]$  is doped with only one second n-dopant, different from the first dopant, for improving the layer quality of the active layer  $[(18)]$ .

~~Figure 1--~~